



PQMD10

NPN/PNP resistor-equipped transistors;
 $R1 = 2.2 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

15 April 2025

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PQMH10

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

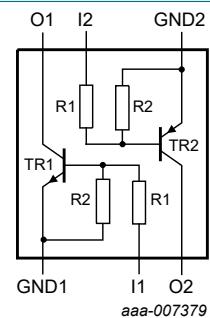
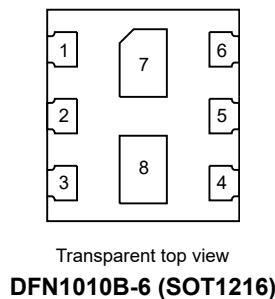
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
V_{CEO}	collector-emitter voltage	open base		-	-	50	V
I_o	output current			-	-	100	mA
R1	bias resistor 1 (input)	$T_{amb} = 25 \text{ }^\circ\text{C}$	[1]	1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		[1]	17	21	26	

[1] See section "Test information" for resistor calculation and test conditions.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		
2	I1	input (base) TR1		
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		
5	I2	input (base) TR2		
6	O1	output (collector) TR1		
7	O1	output (collector) TR1		
8	O2	output (collector) TR2		



6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PQMD10	DFN1010B-6	plastic, leadless thermal enhanced ultra thin small outline package; 6 terminals; 0.35 mm pitch; 1.1 mm x 1 mm x 0.37 mm body	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
PQMD10	B 010

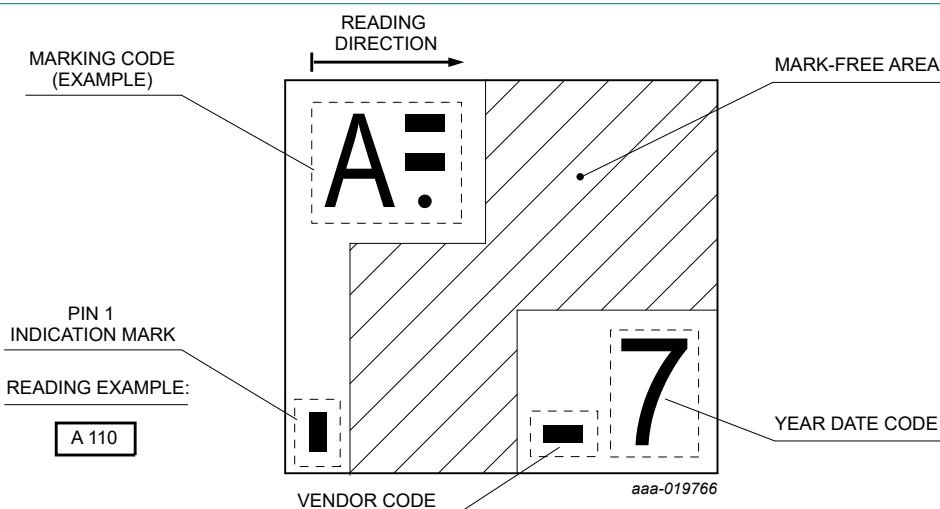


Fig. 1. DFN1010B-6 (SOT1216) binary marking code description

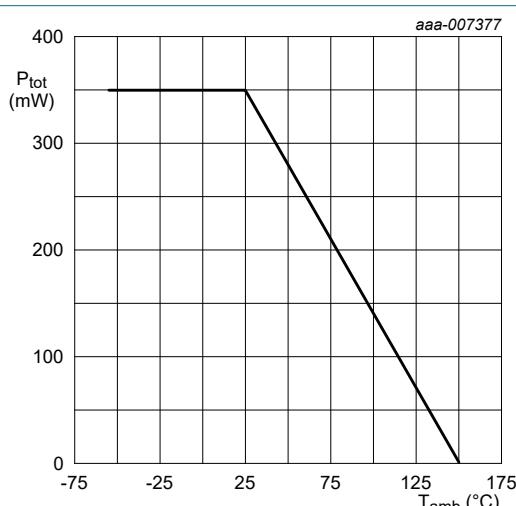
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
V_I	input voltage	TR1; positive		-	12	V
		TR1; negative		-	-5	V
		TR2; positive		-	5	V
		TR2; negative		-	-12	V
I_O	output current			-	100	mA
I_{CM}	peak collector current	$t_p \leq 1 \text{ ms}$; single pulse		-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ\text{C}$	[1]	-	230	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ\text{C}$	[1]	-	350	mW
T_j	junction temperature			-	150	$^\circ\text{C}$
T_{amb}	ambient temperature			-55	150	$^\circ\text{C}$
T_{stg}	storage temperature			-65	150	$^\circ\text{C}$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

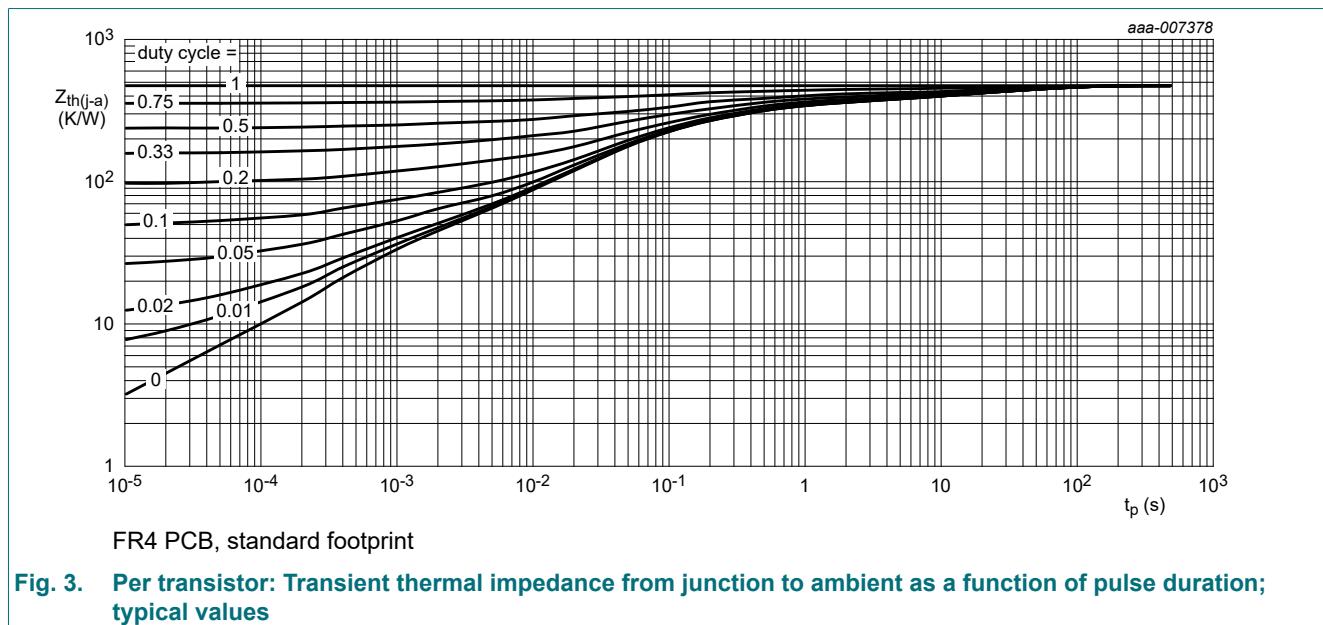
Fig. 2. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



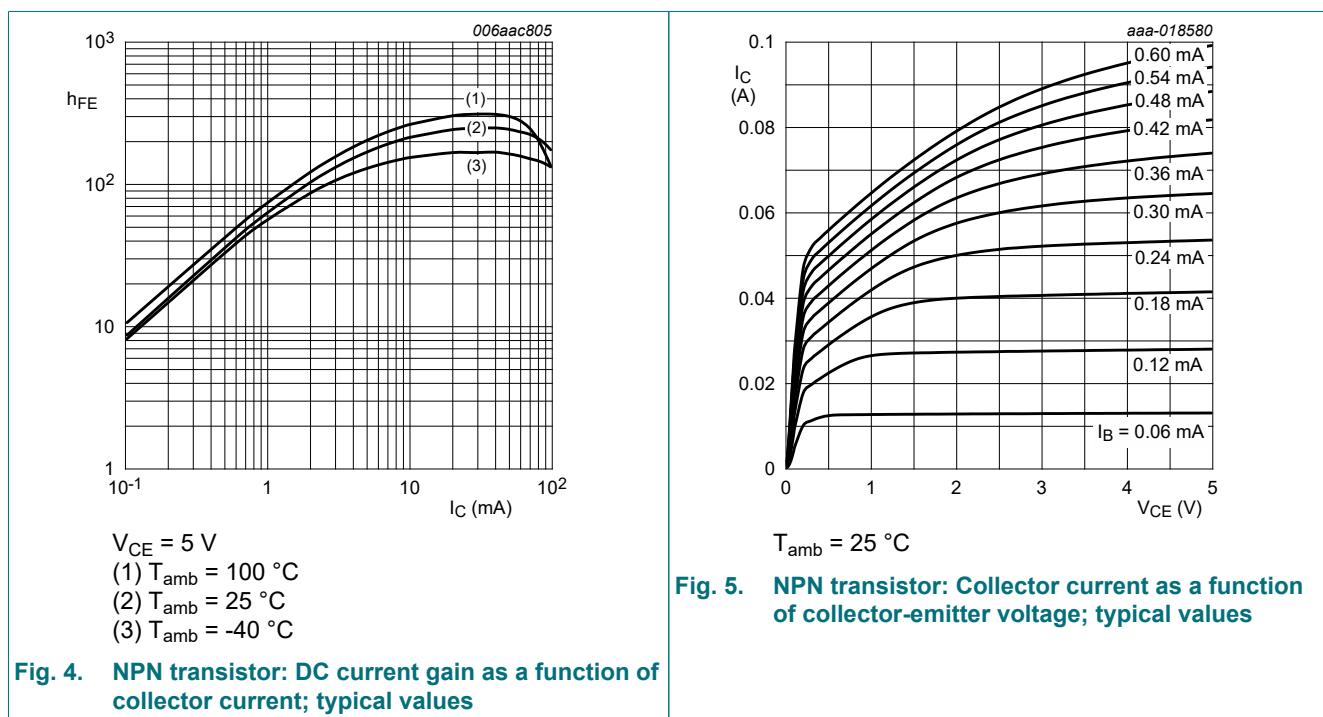
10. Characteristics

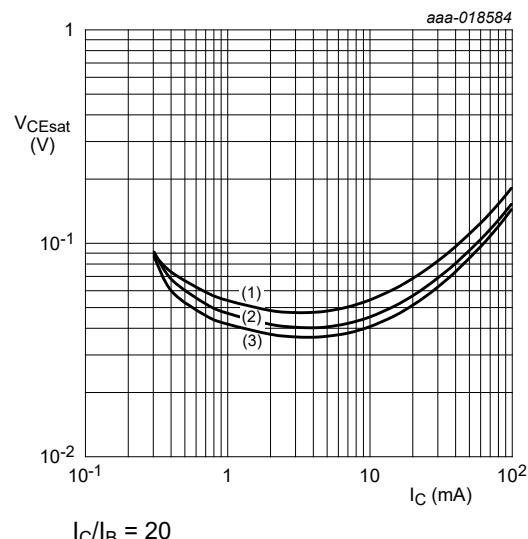
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
I_{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}$; $I_E = 0 \text{ A}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$; $I_B = 0 \text{ A}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		-	-	1	μA
		$V_{CE} = 30 \text{ V}$; $I_B = 0 \text{ A}$; $T_{amb} = 150 \text{ }^\circ\text{C}$		-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}$; $I_C = 0 \text{ A}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		-	-	180	μA
h_{FE}	DC current gain	$V_{CE} = 5 \text{ V}$; $I_C = 10 \text{ mA}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		100	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}$; $I_B = 0.25 \text{ mA}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}$; $I_C = 100 \mu\text{A}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}$; $I_C = 5 \text{ mA}$; $T_{amb} = 25 \text{ }^\circ\text{C}$		1.1	0.75	-	V
$R1$	bias resistor 1 (input)	$T_{amb} = 25 \text{ }^\circ\text{C}$	[1]	1.54	2.2	2.86	$\text{k}\Omega$
$R2/R1$	bias resistor ratio		[1]	17	21	26	
C_c	collector capacitance	$V_{CB} = 10 \text{ V}$; $I_E = 0 \text{ A}$; $f = 1 \text{ MHz}$; $T_{amb} = 25 \text{ }^\circ\text{C}$; TR1 (NPN)		-	-	2.5	pF
		$V_{CB} = -10 \text{ V}$; $I_E = 0 \text{ A}$; $f = 1 \text{ MHz}$; $T_{amb} = 25 \text{ }^\circ\text{C}$; TR2 (PNP)		-	-	3	pF
f_T	transition frequency	$V_{CE} = 5 \text{ V}$; $I_C = 10 \text{ mA}$; $f = 100 \text{ MHz}$; $T_{amb} = 25 \text{ }^\circ\text{C}$; TR1 (NPN)	[2]	-	230	-	MHz
		$V_{CE} = -5 \text{ V}$; $I_C = -10 \text{ mA}$; $f = 100 \text{ MHz}$; $T_{amb} = 25 \text{ }^\circ\text{C}$; TR2 (PNP)	[2]	-	180	-	MHz

[1] See section "Test information" for resistor calculation and test conditions.

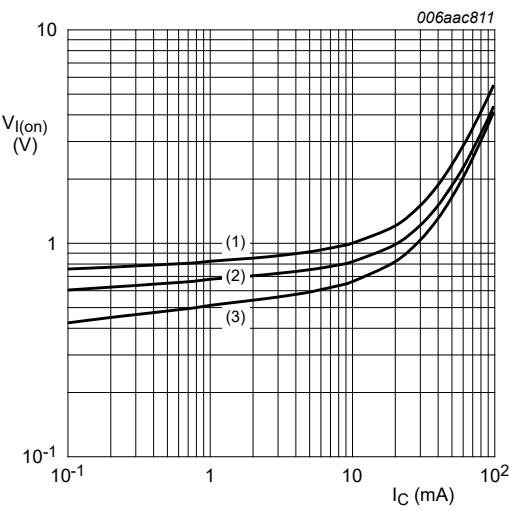
[2] Characteristics of built-in transistor





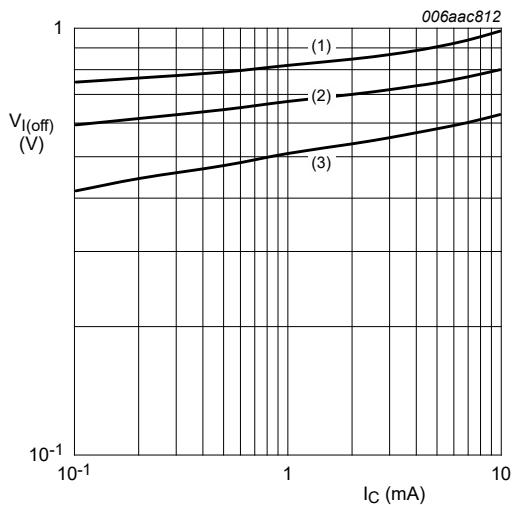
$I_C/I_B = 20$
 (1) $T_{\text{amb}} = 100 \text{ }^{\circ}\text{C}$
 (2) $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$
 (3) $T_{\text{amb}} = -40 \text{ }^{\circ}\text{C}$

Fig. 6. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



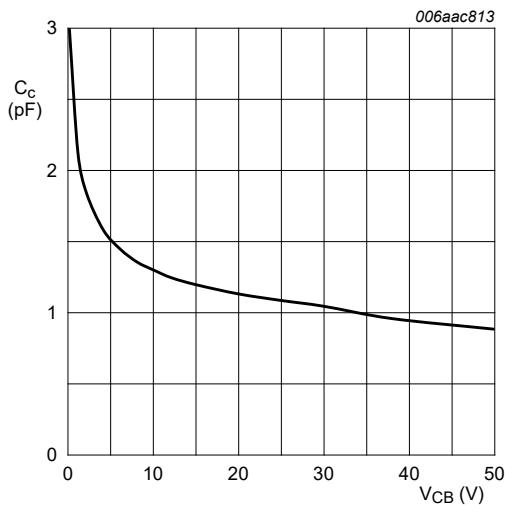
$V_{CE} = 0.3 \text{ V}$
 (1) $T_{\text{amb}} = -40 \text{ }^{\circ}\text{C}$
 (2) $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$
 (3) $T_{\text{amb}} = 100 \text{ }^{\circ}\text{C}$

Fig. 7. NPN transistor: On-state input voltage as a function of collector current; typical values



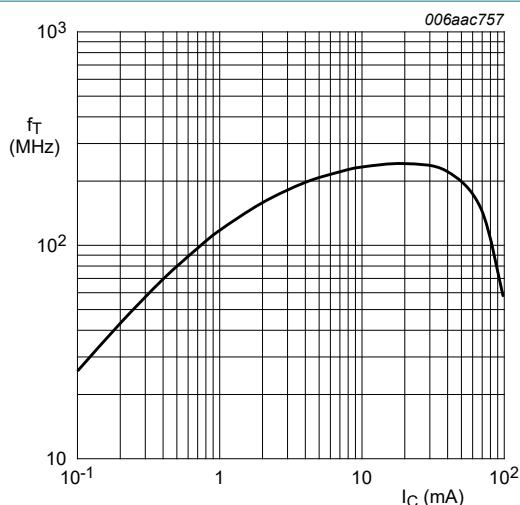
$V_{CE} = 5 \text{ V}$
 (1) $T_{\text{amb}} = -40 \text{ }^{\circ}\text{C}$
 (2) $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$
 (3) $T_{\text{amb}} = 100 \text{ }^{\circ}\text{C}$

Fig. 8. NPN transistor: Off-state input voltage as a function of collector current; typical values



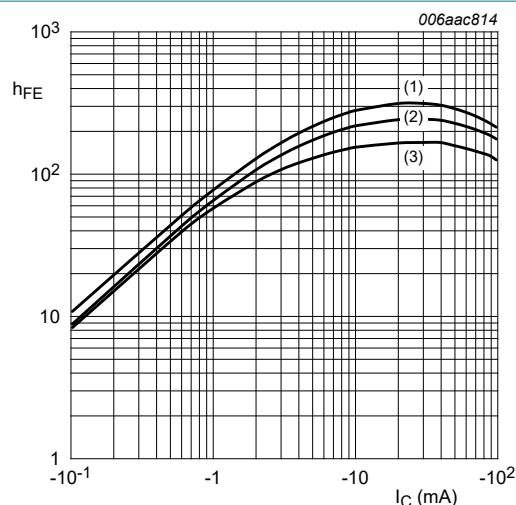
$f = 1 \text{ MHz}; T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$

Fig. 9. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = 5 \text{ V}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$

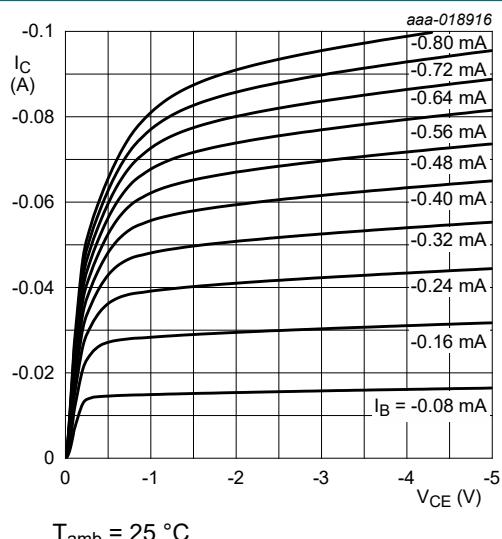
Fig. 10. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



$V_{CE} = -5 \text{ V}$

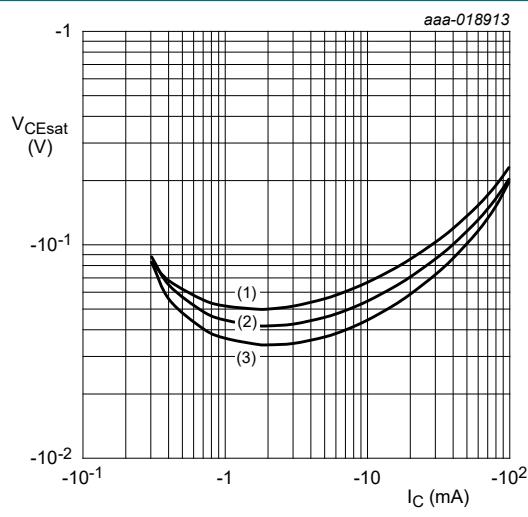
- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$

Fig. 11. PNP transistor: DC current gain as a function of collector current; typical values



$T_{amb} = 25 \text{ }^{\circ}\text{C}$

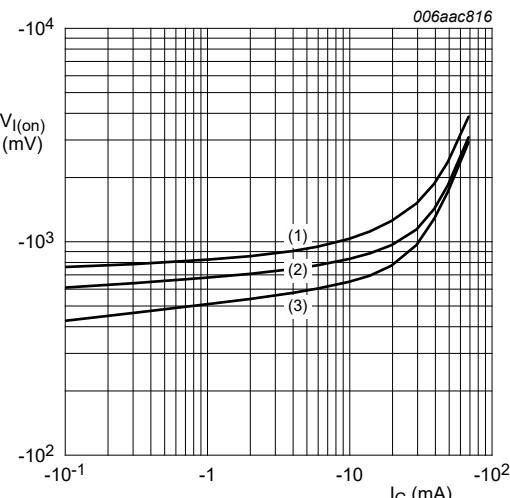
Fig. 12. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



$I_C/I_B = 20$

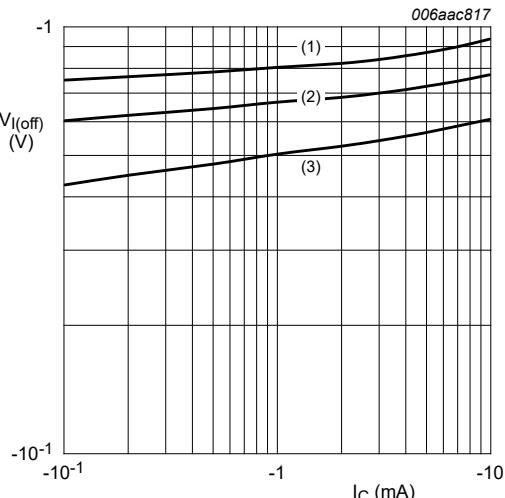
- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$

Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



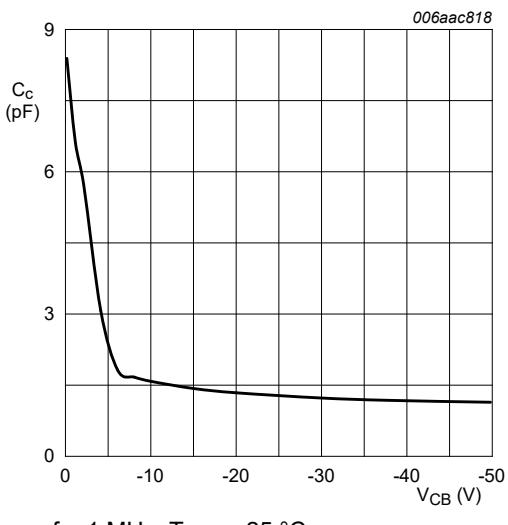
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$

Fig. 14. PNP transistor: On-state input voltage as a function of collector current; typical values



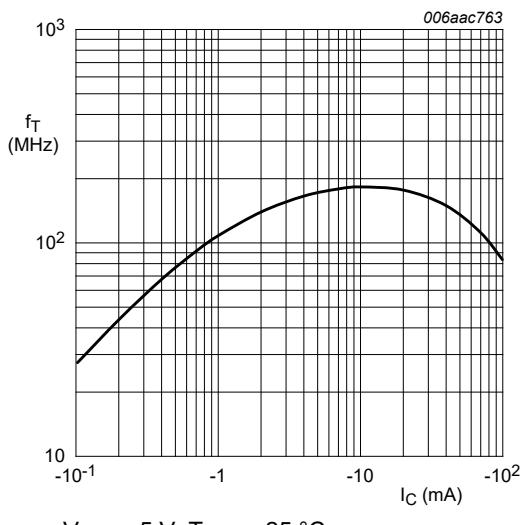
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$

Fig. 15. PNP transistor: Off-state input voltage as a function of collector current; typical values



$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig. 16. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig. 17. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

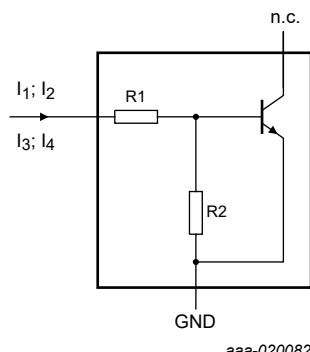
Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R_1 = \frac{V(I_2) - V(I_1)}{I_2 - I_1}$$

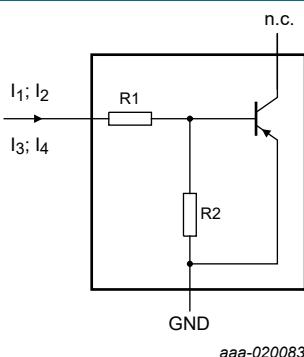
- Calculation of bias resistor ratio (R2/R1)

$$\frac{R_2}{R_1} = \frac{V(I_4) - V(I_3)}{R_1 \cdot (I_4 - I_3)} - 1$$



aaa-020082

Fig. 18. NPN transistor: Resistor test circuit



aaa-020083

Fig. 19. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

Product	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	I ₂	I ₃	I ₄
TR1 (NPN)	2.2	47	90 µA	140 µA	-55 µA	-105 µA
TR2 (PNP)	2.2	47	-90 µA	-140 µA	55 µA	105 µA

12. Package outline

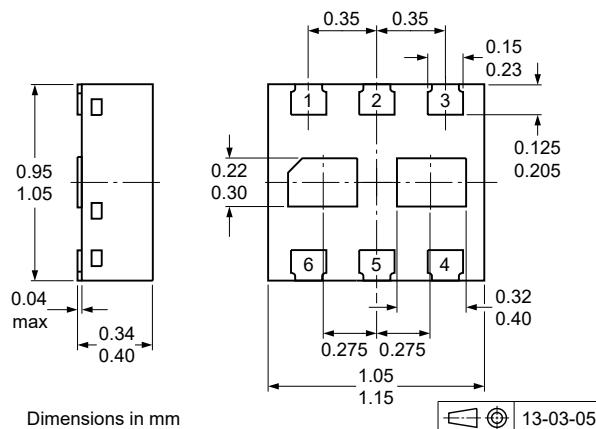


Fig. 20. Package outline DFN1010B-6 (SOT1216)

13. Soldering

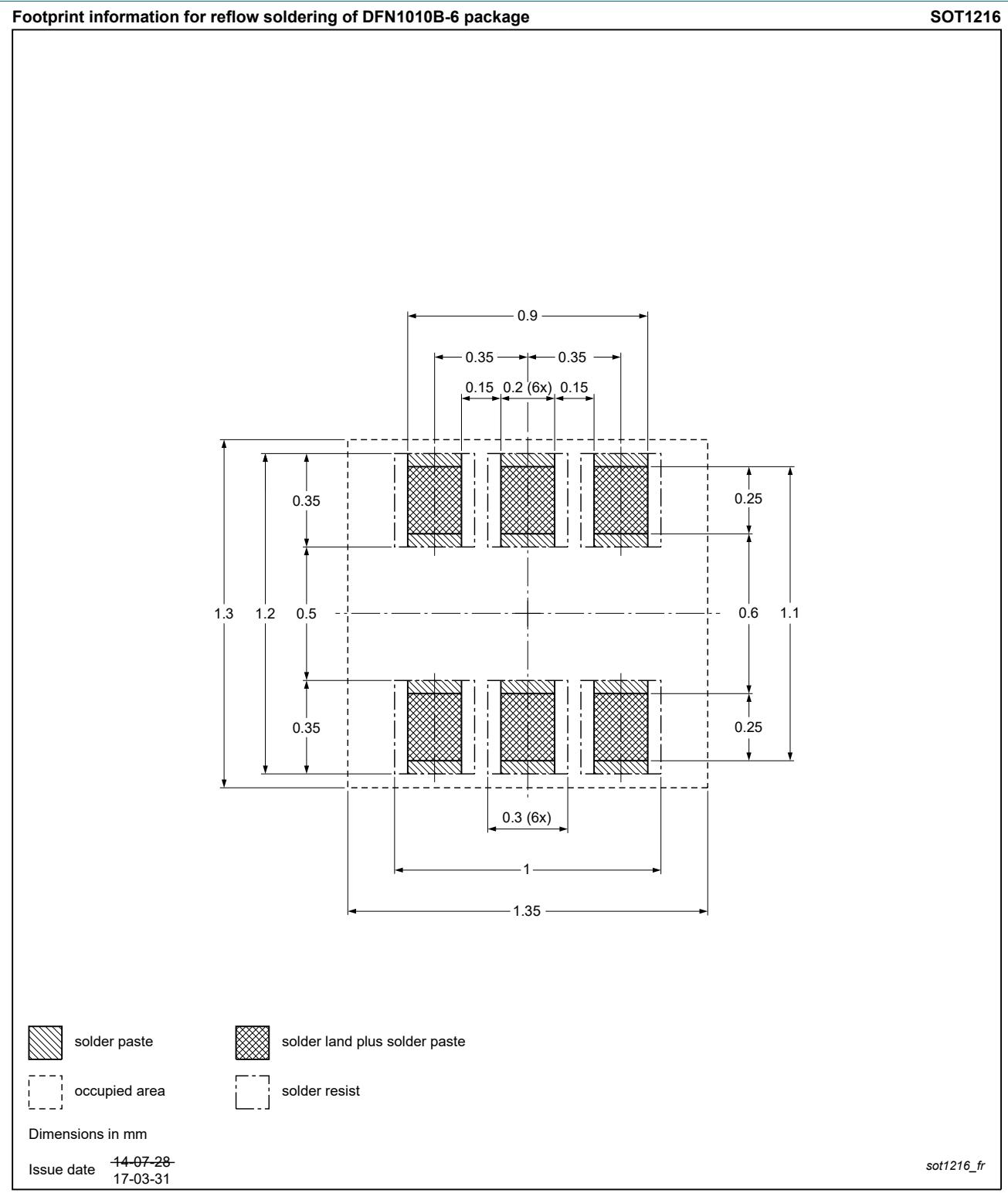


Fig. 21. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMD10 v.2	20250415	Product data sheet	-	PQMD10 v.1
Modifications:	<ul style="list-style-type: none">Soldering changed			
PQMD10 v.1	20151104	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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